## **MOTOR01028**-10FP供应商 SEMICONDUCTOR TECHNICAL DATA

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by MAC228FP/D

# WWW.DZSC.COM Triacs Silicon Bidirectional Triode Thyristors

... designed primarily for industrial and consumer applications for full wave control of ac loads such as appliance controls, heater controls, motor controls, and other power switching applications.

- Four Mode Triggering for Drive Circuits that Source Current
- All Diffused and Glass-Passivated Junctions for Parameter Uniformity and Stability •
- Small, Rugged, Thermowatt Construction for Low Thermal resistance and High Heat Dissipation
- Center Gate Geometry for Uniform Current Spreading



TRIACs **8 AMPERES RMS** 200 thru 800 VOLTS





MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted.)

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Rating	Rating Symbol		Unit	
Peak Repetitive Off-State Voltage <sup>(1)</sup> ( $T_J = -40$ to 110°C 1/2 Sine Wave 50 to 60 Hz, Gate Open) MAC228-4FP, MAC228A4FP MAC228-6FP, MAC228A6FP MAC228-8FP, MAC228A8FP MAC228-10FP, MAC228A10FP	VDRM	200 400 600 800	Volts	
On-State RMS Current (T <sub>C</sub> = 80°C) Full Cycle Sine Wave 50 to 60 Hz	IT(RMS)	8	Amps	
Peak Non-repetitive Surge Current (One Full Cycle 60 Hz, T <sub>J</sub> = 110°C)	ITSM	80	Amps	
Circuit Fusing (t = 8.3 ms)	l <sup>2</sup> t	26	A <sup>2</sup> s	
Peak Gate Current (t ≤ 2 μs)	IGM	I <sub>GM</sub> ±2		
Peak Gate Voltage (t ≤ 2 μs)	VGM	V <sub>GM</sub> ±10		
Peak Gate Power (t ≤ 2 μs)	PGM	P <sub>GM</sub> 20		
Average Gate Power (T <sub>C</sub> = 80°C, t ≤ 8.3 ms)	PG(AV)	0.5	Watts	
Operating Junction Temperature Range	Тј	-40 to 110	°C	
Storage Temperature Range	T <sub>stg</sub>	-40 to 150	°C	
Mounting Torque		8	in. lb.	

1. VDRM for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

The case temperature reference point for all TC measurements is a point on the center lead of the package as close as possible to the plastic body.

### **MAC228FP Series MAC228AFP Series**

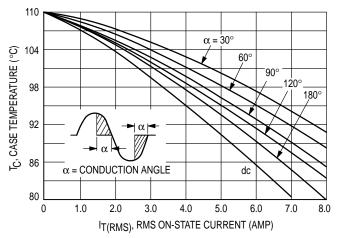
#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	2.2	°C/W
Thermal Resistance, Case to Sink	R <sub>0CS</sub>	2.2 (typ)	°C/W
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	60	°C/W

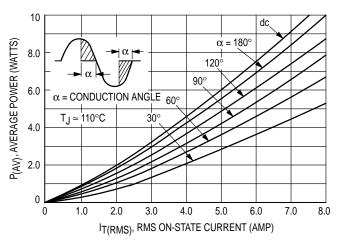
**ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$  and either polarity of MT2 to MT1 voltage unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
Peak Blocking Current (V <sub>D</sub> = Rated V <sub>DRM</sub> , Gate Open) T <sub>J</sub> = 25°C T <sub>J</sub> = 110°C	IDRM			10 2	μA mA
Peak On-State Voltage (ITM = 11 A Peak, Pulse Width $\leq$ 2 ms, Duty Cycle $\leq$ 2%)	VTM	—	-	1.8	Volts
Gate Trigger Current (Continuous dc) $(V_D = 12 V, R_L = 100 \Omega)$ MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+) "A" Suffix Only	IGT			5 10	mA
Gate Trigger Voltage (Continuous dc) $(V_D = 12 V, R_L = 100 \Omega)$ MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+) "A" Suffix Only $(V_D = Rated V_{DRM}, T_C = 110^{\circ}C, R_L = 10 k)$ MT2(+), G(+); MT2(+), G(-); MT2(-), G(-) MT2(-), G(+) "A" Suffix Only	VGT	  0.2 0.2	 	2 2.5 —	Volts
Holding Current (V <sub>D</sub> = 12 Vdc, I <sub>TM</sub> = 200 mA, Gate Open)	ΙΗ	-	_	15	mA
Gate-Controlled Turn-On Time ( $V_D$ = Rated $V_{DRM}$ , I <sub>TM</sub> = 16 A Peak, I <sub>G</sub> = 30 mA)	tgt	—	1.5	-	μs
Critical Rate of Rise of Off-State Voltage (V <sub>D</sub> = Rated V <sub>DRM</sub> , Exponential Waveform, T <sub>C</sub> = 110°C)	dv/dt	—	25	_	V/µs
Critical Rate of Rise of Commutation Voltage (V <sub>D</sub> = Rated V <sub>DRM</sub> , I <sub>TM</sub> = 11.3 A, Commutating di/dt = 4.1 A/ms, Gate Unenergized, T <sub>C</sub> = 80°C)	dv/dt(c)	_	5	_	V/µs



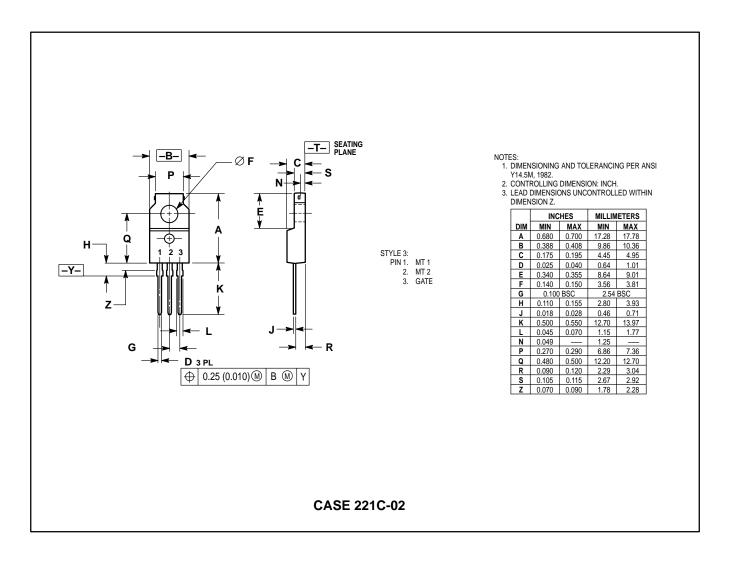


#### FIGURE 2 - ON-STATE POWER DISSIPATION



#### **MAC228FP Series MAC228AFP Series**

#### PACKAGE DIMENSIONS



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